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Free DownloadCA ERwin Data Modeler: CA ERwin Data Modeler was developed to be a user-friendly tool that provides a powerful model design and development environment. This invention relates to a semiconductor memory device of high memory capacity and the method of manufacturing the same, and more particularly to a non-volatile memory device which enables a high density circuit integration, a high speed operation, and a low power dissipation and to the method of manufacturing the same. In recent years, an explosive increase in the amount of information to be stored has raised a strong demand for a large capacity memory device. By increasing the memory cell size, the capacitance of each memory cell can be increased. However, the integration density in integrated circuit devices (e.g. LSI devices) has a tendency to be decreased to reduce the manufacturing cost. A method for overcoming this problem has been proposed in U.S. Pat. No. 3,984,822, wherein the thickness of a silicon dioxide film constituting the gate insulation film is reduced and the effective gate length is thereby increased so as to increase the capacitance. This method, however, is undesirable because the manufacturing cost of the memory device becomes expensive. In contrast, U.S. Pat. No. 4,174,383 discloses a memory device which is manufactured by using a stacked structure of ferroelectric ceramic layers as a capacitor. This ferroelectric ceramic layers can be formed at a low temperature in a short period of time, and therefore the manufacture of the memory device at a low cost is possible. Such a

